



# 18-BIT, 1-MSPS, PSEUDO-DIFFERENTIAL UNIPOLAR INPUT, MICROPOWER SAMPLING ANALOG-TO-DIGITAL CONVERTER WITH PARALLEL INTERFACE AND REFERENCE

### **FEATURES**

- 0 to 1 MSPS Sampling Rate
- 18-Bit NMC Ensured Over Temperature
- Low ±0.1 mV Offset Error
- Low 0.2 ppm/°C Offset Error Temperature Drift
- Low 0.6 ppm/°C Gain Error Temperature Drift
- Zero Latency
- Low Power: 220 mW at 1 MSPS
- Unipolar Single-Ended Input Range: 0 V to V<sub>ref</sub>
- Onboard Reference
- Onboard Reference Buffer
- High-Speed Parallel Interface
- Wide Digital Supply 2.7 V ~ 5.25 V
- 8-/16-/18-Bit Bus Transfer
- 7x7 QFN Package

## **APPLICATIONS**

- Medical Instruments
- Optical Networking
- Transducer Interface
- High Accuracy Data Acquisition Systems
- Magnetometers

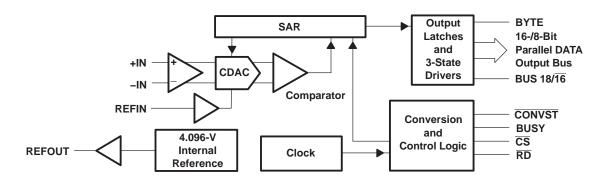
## **DESCRIPTION**

The ADS8481 is an 18-bit, 1-MSPS A/D converter with an internal 4.096-V reference and a pseudo-differential unipolar single-ended input. The device includes a 18-bit capacitor-based SAR A/D converter with inherent sample and hold. The ADS8481 offers a full 18-bit interface, a 16-bit option where data is read using two read cycles, or an 8-bit bus option using three read cycles.

The ADS8481 is available in a 7x7 QFN package and is characterized over the industrial -40°C to 85°C temperature range.

## HIGH SPEED SAR CONVERTER FAMILY

TYPE/SPEED	500 kHz	580 kHz	750 kHz	1 MHz	1.25 MHz	2 MHz	3 MHz	4MHz
18-Bit Pseudo-Diff	ADS8383	ADS8381		ADS8481				
10-Bit Fseudo-Dill		ADS8380(S)						
18-Bit Pseudo-Bipolar, Fully Diff		ADS8382(S)		ADS8482				
16-Bit Pseudo-Diff			ADS8371	ADS8471	ADS8401	ADS8411		
To-Bit Pseudo-Dill					ADS8405			
16 Dit Doordo Binolay Fully Diff				ADS8472	ADS8402	ADS8412		
16-Bit Pseudo-Bipolar, Fully Diff					ADS8406			
14-Bit Pseudo-Diff					ADS7890 (s)		ADS7891	
12-Bit Pseudo-Diff				ADS7886		ADS7883		ADS7881





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ORDERING INFORMATION(1)

MODEL	MAXIMUM INTEGRAL LINEARITY (LSB)	MAXIMUM DIFFERENTIAL LINEARITY (LSB)	NO MISSING CODES RESOLUTION (BIT)	PACKAGE TYPE	PACKAGE DESIGNATOR	TEMPER- ATURE RANGE	ORDERING INFORMATION	TRANS- PORT MEDIA QTY.				
ADS8481I	±5	−1 to +2.5	18	7x7 48 Pin	RGZ	–40°C to	ADS8482IRGZT	Tape and reel 250				
AD364611	±3	-1 10 +2.5	10	QFN		NOZ	85°C	ADS8481IRGZR	Tape and reel 1000			
ADC0404ID	0.5	4. 45	4. 45	40	7x7 48 Pin	7x7 48 Pin	7x7 48 Pin	D07	507	–40°C to	ADS8481IBRGZT	Tape and reel 250
ADS8481IB	±3.5	−1 to +1.5	18	QFN RGZ		QFN RGZ		85°C	ADS8481IBRGZR	Tape and reel 1000		

<sup>(1)</sup> For the most current specifications and package information, refer to our website at www.ti.com.

## **ABSOLUTE MAXIMUM RATINGS**(1)

over operating free-air temperature range (unless otherwise noted)

			VALUE	UNIT
		+IN to AGND	-0.4 to +VA + 0.1	V
		-IN to AGND	-0.4 to 0.5	V
	Voltage	+VA to AGND	-0.3 to 7	V
		+VBD to BDGND		V
		+VA to +VBD	-0.3 to 2.55	V
	Digital input voltage to BDGND		-0.3 to +VBD + 0.3	V
	Digital output voltage to BDGNI	)	-0.3 to +VBD + 0.3	V
T <sub>A</sub>	Operating free-air temperature	ange	-40 to 85	°C
T <sub>stg</sub>	Storage temperature range		-65 to 150	°C
	Junction temperature (T <sub>J</sub> max)		150	°C
	OEN package	Power dissipation	$(T_J Max - T_A)/\theta_{JA}$	
	QFN package	$\theta_{JA}$ thermal impedance	22	°C/W
	Load tomporature coldering	Vapor phase (60 sec)	215	°C
	Lead temperature, soldering	Infrared (15 sec)	220	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



## **SPECIFICATIONS**

 $T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C}, \, \text{+VA} = 5 \,\, \text{V}, \, \text{+VBD} = 3 \,\, \text{V or 5 V}, \, V_{\text{ref}} = 4.096 \,\, \text{V}, \, f_{\text{SAMPLE}} = 1 \,\, \text{MSPS (unless otherwise noted)}$ 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG INPUT						
Full-scale input voltage <sup>(1)</sup>		+IN - (-IN)	0		$V_{ref}$	V
About the force of contrary		+IN	-0.2		V <sub>ref</sub> +0.2	V
Absolute input voltage		-IN	-0.2		0.2	V
Input capacitance				65		pF
Input leakage current				1		nA
SYSTEM PERFORMANCE						
Resolution			18			Bits
No missing codes	ADS8481I		18	18		Bits
No missing codes	ADS8481IB		18			סווט
Integral linearity (2)(3)	ADS8481I		-5	-1.5/+1.9	5	LSB
integral linearity (=7.57	ADS8481IB		-3.5	-1.5/+1.9	3.5	(18 bit)
Differential linearity	ADS8481I		-1	-0.5/+0.7	2.5	LSB (18 bit)
Differential lifearity	ADS8481IB		-1	-0.5/+0.7	1.5	
Offset error <sup>(4)</sup>	ADS8481I		-0.5	±0.1	0.5	mV
Oliset endix 9	ADS8481IB		-0.5	±0.1	0.5	IIIV
Offset error temperature drift				±0.2		ppm/°C
Gain error <sup>(4)(5)</sup>	ADS8481I	V <sub>ref</sub> = 4.096 V	-0.075	±0.05	0.075	%FS
Gaill ellol ( )(3)	ADS8481IB	V <sub>ref</sub> = 4.096 V	-0.075	±0.05	0.075	%FS
Gain error temperature drift				±0.6		ppm/°C
Noise				30		$\mu V \text{ RMS}$
Power supply rejection ratio		At 3FFFFh output code		60		dB
SAMPLING DYNAMICS						
Conversion time				650	710	ns
Acquisition time			250			ns
Throughput rate					1	MHz
Aperture delay				4		ns
Aperture jitter				5		ps
Step response				150		ns
Over voltage recovery				150		ns

<sup>(1)</sup> Ideal input span, does not include gain or offset error.(2) LSB means least significant bit

<sup>(3)</sup> This is endpoint INL, not best fit.

 <sup>(4)</sup> Measured relative to an ideal full-scale input [+IN – (-IN)] of 4.096 V
 (5) This specification does not include the internal reference voltage error and drift.



## **SPECIFICATIONS (Continued)**

 $T_A = -40$ °C to 85°C, +VA = 5 V, +VBD = 3 V or 5 V,  $V_{ref} = 4.096$  V,  $f_{SAMPLE} = 1$  MSPS (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN TYP I	MAX	UNIT	
DYNAMIC CHARACTERISTICS						
	ADS8481I	\/	-110			
	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 1 kHz	-112			
Total harmonia distortion (TLID)(1)	ADS8481I	\/ 4\/ at 10 kHz	-106		٩D	
Total harmonic distortion (THD) <sup>(1)</sup>	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 10 kHz	-108		dB	
	ADS8481I	\/ 4\/ at 100 kHz	-98			
	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 100 kHz	-99			
	ADS8481I	\/ _ 4 \/ _ at 1 kHz	92			
Signal to noise ratio (SNR) <sup>(1)</sup>	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 1 kHz	94			
	ADS8481I	\/ - 4\/ at 10 kHz	91		dB	
Signal to hoise fatto (SNK)	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 10 kHz	93		uБ	
	ADS8481I	\/ 4\/ at 400 ld l=	90			
	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 100 kHz	92			
	ADS8481I	\/ - 4 \/ ot 1 kHz	91			
	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 1 kHz	93			
Cinnal to mains a distantian (CINIAD)(1)	ADS8481I	V 4V -140111-	90		dB	
Signal to noise + distortion (SINAD) <sup>(1)</sup>	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 10 kHz	92			
	ADS8481I	\/ 4\/ at 100 kHz	89			
	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 100 kHz	91			
	ADS8481I	\/ 4\/ ot 4 kl l=	110			
	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 1 kHz	112			
Courious from dunamia range (CEDD) (1)	ADS8481I	\/ 4\/ at 40 kHz	108		٩D	
Spurious free dynamic range (SFDR) <sup>(1)</sup>	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 10 kHz	107		dB	
	ADS8481I	\/ - 4\/ ot 400 kHz	98			
	ADS8481IB	$V_{IN} = 4 V_{pp}$ at 100 kHz	98			
-3dB Small signal bandwidth			15		MHz	
VOLTAGE REFERENCE INPUT						
Reference voltage at REFIN, Vref			3.0 4.096	4.2	V	
Reference resistance <sup>(2)</sup>			500		kΩ	
Reference current drain		f <sub>s</sub> = 1 MHz		1	mA	

<sup>(1)</sup> Calculated on the first nine harmonics of the input frequency.(2) Can vary ±20%



## **SPECIFICATIONS (Continued)**

 $T_A = -40$ °C to 85°C, +VA = 5 V, +VBD =  $\frac{3}{2}$  V or 5 V,  $V_{ref} = 4.096$  V,  $f_{SAMPLE} = 1$  MSPS (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
INTERNAL RE	FERENCE OUTPUT						
Internal reference start-up time		From 95% (+VA), with 1-µF storage capacitor			120	ms	
Reference volta	age range, V <sub>ref</sub>	I <sub>O</sub> = 0 A	4.081	4.096	4.111	V	
Source current		Static load			10	μΑ	
Line regulation		+VA = 4.75 V to 5.25 V		60		μV	
Drift		I <sub>O</sub> = 0 A		±6		PPM/C	
DIGITAL INPU	T/OUTPUT		,				
Logic family – 0	CMOS						
	V <sub>IH</sub>	I <sub>IH</sub> = 5 μA	+VBD-1		+V <sub>BD</sub> +0.3		
l ania laval	V <sub>IL</sub>	I <sub>IL</sub> = 5 μA	-0.3		0.8	V	
Logic level	V <sub>OH</sub>	I <sub>OH</sub> = 2 TTL loads	+V <sub>BD</sub> - 0.6			V	
	V <sub>OL</sub>	I <sub>OL</sub> = 2 TTL loads			0.4		
Data format – S	Straight Binary						
POWER SUPP	LY REQUIREMENT	S					
Power supply	+VBD		2.7	3.3	5.25	V	
voltage	+VA		4.75	5	5.25	V	
Supply current	(1)	f <sub>s</sub> = 1 MHz		44	48	mA	
Power dissipati	on <sup>(1)</sup>	f <sub>S</sub> = 1 MHz		220	240	mW	
TEMPERATUR	RE RANGE		•				
Operating free-	air		-40		85	°C	

<sup>(1)</sup> This includes only +VA current. +VBD current is typical 1 mA with 5 pF load capacitance on all output pins.



## **TIMING CHARACTERISTICS**

All specifications typical at  $-40^{\circ}$ C to  $85^{\circ}$ C, +VA = +VBD = 5 V (1)(2)(3)

	PARAMETER	MIN	TYP I	ИΑХ	UNIT
t <sub>(CONV)</sub>	Conversion time			710	ns
t <sub>(ACQ)</sub>	Acquisition time	250			ns
t <sub>(HOLD)</sub>	Sample capacitor hold time			25	ns
t <sub>pd1</sub>	CONVST low to BUSY high			40	ns
t <sub>pd2</sub>	Propagation delay time, end of conversion to BUSY low			15	ns
t <sub>pd3</sub>	Propagation delay time, start of convert state to rising edge of BUSY			15	ns
t <sub>w1</sub>	Pulse duration, CONVST low	40			ns
t <sub>su1</sub>	Setup time, CS low to CONVST low	20			ns
t <sub>w2</sub>	Pulse duration, CONVST high	20			ns
	CONVST falling edge jitter			10	ps
t <sub>w3</sub>	Pulse duration, BUSY signal low	t <sub>(ACQ)</sub> min			ns
t <sub>w4</sub>	Pulse duration, BUSY signal high			710	ns
t <sub>h1</sub>	Hold time, first data bus transition (RD low, or CS low for read cycle, or BYTE or BUS18/16 input changes) after CONVST low	40			ns
t <sub>d1</sub>	Delay time, $\overline{\text{CS}}$ low to $\overline{\text{RD}}$ low	0			ns
t <sub>su2</sub>	Setup time, RD high to CS high	0			ns
t <sub>w5</sub>	Pulse duration, RD low	50			ns
t <sub>en</sub>	Enable time, RD low (or CS low for read cycle) to data valid			20	ns
t <sub>d2</sub>	Delay time, data hold from RD high	5			ns
t <sub>d3</sub>	Delay time, BUS18/16 or BYTE rising edge or falling edge to data valid	10		20	ns
t <sub>w6</sub>	Pulse duration, RD high	20			ns
t <sub>w7</sub>	Pulse duration, CS high	20			ns
t <sub>h2</sub>	Hold time, last RD (or CS for read cycle ) rising edge to CONVST falling edge	50			ns
t <sub>pd4</sub>	Propagation delay time, BUSY falling edge to next $\overline{\text{RD}}$ (or $\overline{\text{CS}}$ for read cycle) falling edge	0			ns
t <sub>d4</sub>	Delay time, BYTE edge to BUS18/16 edge skew	0			ns
t <sub>su3</sub>	Setup time, BYTE or BUS18/16 transition to RD falling edge	10			ns
t <sub>h3</sub>	Hold time, BYTE or BUS18/16 transition to RD falling edge	10			ns
t <sub>dis</sub>	Disable time, RD high (CS high for read cycle) to 3-stated data bus			20	ns
t <sub>d5</sub>	Delay time, BUSY low to MSB data valid delay			0	ns
t <sub>d6</sub>	Delay time, CS rising edge to BUSY falling edge	50			ns
t <sub>d7</sub>	Delay time, BUSY falling edge to CS rising edge	50			ns
t <sub>su5</sub>	BYTE transition setup time, from BYTE transition to next BYTE transition, or BUS18/ $\overline{16}$ transition setup time, from BUS18/ $\overline{16}$ to next BUS18/ $\overline{16}$ .	50			ns
t <sub>su(ABORT)</sub>	Setup time from the falling edge of $\overline{CONVST}$ (used to start the valid conversion) to the next falling edge of $\overline{CONVST}$ (when $\overline{CS}$ is used to abort).	60		610	ns

 <sup>(1)</sup> All input signals are specified with t<sub>r</sub> = t<sub>f</sub> = 5 ns (10% to 90% of +VBD) and timed from a voltage level of (V<sub>IL</sub> + V<sub>IH</sub>)/2.
 (2) See timing diagrams.
 (3) All timing are measured with 20-pF equivalent loads on all data bits and BUSY pins.



## **TIMING CHARACTERISTICS**

All specifications typical at -40°C to 85°C,  $+VA = 5 V + VBD = 3 V <math>^{(1)(2)(3)}$ 

	PARAMETER	MIN	TYP	MAX	UNIT
t <sub>(CONV)</sub>	Conversion time			710	ns
t <sub>(ACQ)</sub>	Acquisition time	250			ns
t <sub>(HOLD)</sub>	Sample capacitor hold time			25	ns
t <sub>pd1</sub>	CONVST low to BUSY high			40	ns
t <sub>pd2</sub>	Propagation delay time, end of conversion to BUSY low			25	ns
t <sub>pd3</sub>	Propagation delay time, start of convert state to rising edge of BUSY			25	ns
t <sub>w1</sub>	Pulse duration, CONVST low	40			ns
t <sub>su1</sub>	Setup time, $\overline{\text{CS}}$ low to $\overline{\text{CONVST}}$ low	20			ns
t <sub>w2</sub>	Pulse duration, CONVST high	20			ns
	CONVST falling edge jitter			10	ps
t <sub>w3</sub>	Pulse duration, BUSY signal low	t <sub>(ACQ)</sub> min			ns
t <sub>w4</sub>	Pulse duration, BUSY signal high			710	ns
t <sub>h1</sub>	Hold time, first data bus transition (RD low, or CS low for read cycle, or BYTE or BUS18/16 input changes) after CONVST low	40			ns
t <sub>d1</sub>	Delay time, $\overline{\text{CS}}$ low to $\overline{\text{RD}}$ low	0			ns
t <sub>su2</sub>	Setup time, RD high to CS high	0			ns
t <sub>w5</sub>	Pulse duration, RD low	50			ns
t <sub>en</sub>	Enable time, RD low (or CS low for read cycle) to data valid			30	ns
t <sub>d2</sub>	Delay time, data hold from RD high	5			ns
t <sub>d3</sub>	Delay time, BUS18/16 or BYTE rising edge or falling edge to data valid	10		30	ns
t <sub>w6</sub>	Pulse duration, RD high	20			ns
t <sub>w7</sub>	Pulse duration, CS high	20			ns
t <sub>h2</sub>	Hold time, last RD (or CS for read cycle ) rising edge to CONVST falling edge	50			ns
t <sub>pd4</sub>	Propagation delay time, BUSY falling edge to next $\overline{RD}$ (or $\overline{CS}$ for read cycle) falling edge	0			ns
t <sub>d4</sub>	Delay time, BYTE edge to BUS18/16 edge skew	0			ns
t <sub>su3</sub>	Setup time, BYTE or BUS18/16 transition to RD falling edge	10			ns
t <sub>h3</sub>	Hold time, BYTE or BUS18/16 transition to RD falling edge	10			ns
t <sub>dis</sub>	Disable time, RD high (CS high for read cycle) to 3-stated data bus			30	ns
t <sub>d5</sub>	Delay time, BUSY low to MSB data valid delay			0	ns
t <sub>d6</sub>	Delay time, CS rising edge to BUSY falling edge	50			ns
t <sub>d7</sub>	Delay time, BUSY falling edge to CS rising edge	50			ns
t <sub>su5</sub>	BYTE transition setup time, from BYTE transition to next BYTE transition, or BUS18/16 transition setup time, from BUS18/16 to next BUS18/16.	50			ns
t <sub>su(ABORT)</sub>	Setup time from the falling edge of $\overline{CONVST}$ (used to start the valid conversion) to the next falling edge of $\overline{CONVST}$ (when $\overline{CS}$ is used to abort) or to the next falling edge of $\overline{CS}$ (when $\overline{CS}$ is used to abort).	70		620	ns

<sup>(1)</sup> All input signals are specified with  $t_r = t_f = 5$  ns (10% to 90% of +VBD) and timed from a voltage level of  $(V_{IL} + V_{IH})/2$ .

<sup>(2)</sup> See timing diagrams.
(3) All timing are measured with 20-pF equivalent loads on all data bits and BUSY pins.



## **PIN ASSIGNMENTS**

#### **RGZ PACKAGE** (TOP VIEW) BDGND .48 47 46 45 44 43 42 41 40 39 38 37 .36 +VBD +VBD BUS18/16 DB10 2 35 🤇 **BYTE** DB11 ] 3 34 € CONVST DB12 33 RD **DB13** 5 ( 32 € CS DB14 ⊇6 31 C +VA **DB15** 30 € **AGND DB16** 29 ( **AGND** DB17 28 🤇 +VA **AGND** 27 ( **REFM AGND** 26 11 **REFM** 25 14 15 16 17 18 19 20 21 22 23 24 +VA REFOUT Š≷ AGND

NC - No internal connection

NOTE: The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

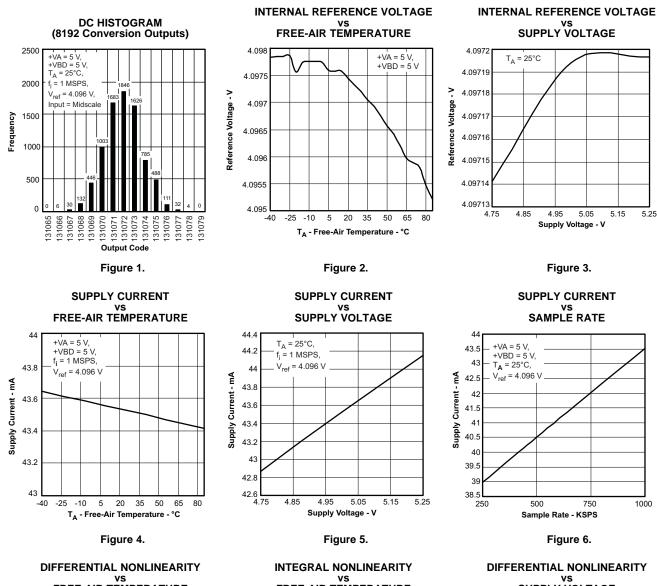


# PIN ASSIGNMENTS (continued) TERMINAL FUNCTIONS

NAME	NO RGZ	I/O			DESCRI	PTION				
AGND	8, 9, 17, 20, 23, 24, 26, 27	-	Analog ground	alog ground						
BDGND	37	-	Digital ground for bus	ital ground for bus interface digital supply						
BUSY	48	0	Status output. High w	us output. High when a conversion is in progress.						
BUS18/ <del>16</del>	2	I	Data bits output or     Last two data bits     a) the low byte pir	ze select input. Used for selecting 18-bit or 16-bit wide bus transfer. a bits output on the 18-bit data bus pins DB[17:0]. t two data bits D[1:0] from 18-bit wide bus output on: he low byte pins DB[9:2] if BYTE = 0 he high byte pins DB[17:10] if BYTE = 1						
BYTE	3	ı	Byte select input. Use 0: No fold back 1: Low byte D[9:2] of		·	to high byte of the	16 most significant	pins DB[17:10].		
CONVST	4	I	Convert start. The fa	ling edge of this inpu	t ends the acquisition	period and starts t	he hold period.			
CS	6	I	Chip select. The falling	ng edge of this input	starts the acquisition	period.				
				8-BIT BUS		16-BI	T BUS	18-BIT BUS		
Data Bus			BYTE = 0	BYTE = 1	BYTE = 1	BYTE = 0	BYTE = 0	BYTE = 0		
			BUS18/16 = 0	BUS18/16 = 0	BUS18/16 = 1	BUS18/16 = 0	BUS18/16 = 1	BUS18/16 = 0		
DB17	28	0	D17 (MSB)	D9	All ones	D17 (MSB)	All ones	D17 (MSB)		
DB16	29	0	D16	D8	All ones	D16	All ones	D16		
DB15	30	0	D15	D7	All ones	D15	All ones	D15		
DB14	31	0	D14	D6	All ones	D14	All ones	D14		
DB13	32	0	D13	D5	All ones	D13	All ones	D13		
DB12	33	0	D12	D4	All ones	D12	All ones	D12		
DB11	34	0	D11	D3	D1	D11	All ones	D11		
DB10	35	0	D10	D2	D0 (LSB)	D10	All ones	D10		
DB9	38	0	D9	All ones	All ones	D9	All ones	D9		
DB8	39	0	D8	All ones	All ones	D8	All ones	D8		
DB7	40	0	D7	All ones	All ones	D7	All ones	D7		
DB6	41	0	D6	All ones	All ones	D6	All ones	D6		
DB5	42	0	D5	All ones	All ones	D5	All ones	D5		
DB4	43	0	D4	All ones	All ones	D4	All ones	D4		
DB3	44	0	D3	All ones	All ones	D3	D1	D3		
DB2	45	0	D2	All ones	All ones	D2	D0 (LSB)	D2		
DB1	46	0	D1	All ones	All ones	D1	All ones	D1		
DB0	47	0	D0 (LSB)	All ones	All ones	D0 (LSB)	All ones	D0 (LSB)		
-IN	19	ı	Inverting input chann	el						
+IN	18	i I	Noninverting input ch							
NC	15	•	No connection							
REFIN	13	1	Reference input							
REFOUT	14	0	Reference output. Ac	ld 1-uF capacitor bety	ween the RFFOLIT n	in and REFM pin wh	nen internal referen	ce is used.		
REFM	11, 12		Reference ground	p. Sapaonoi bott						
RD	5	ı	Synchronization puls	eference ground  ynchronization pulse for the parallel output. When CS is low, this serves as output enable and puts the previous onversion results on the bus.						
+VA	7, 10, 16, 21, 22, 25	_	Analog power supplie							
+VBD	1, 36	_	Digital power supply	for bus						



### TYPICAL CHARACTERISTICS



# FREE-AIR TEMPERATURE

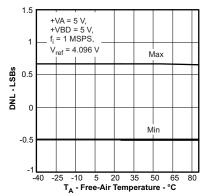


Figure 7.

## FREE-AIR TEMPERATURE

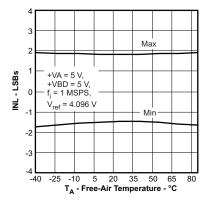


Figure 8.

## SUPPLY VOLTAGE

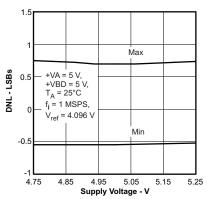
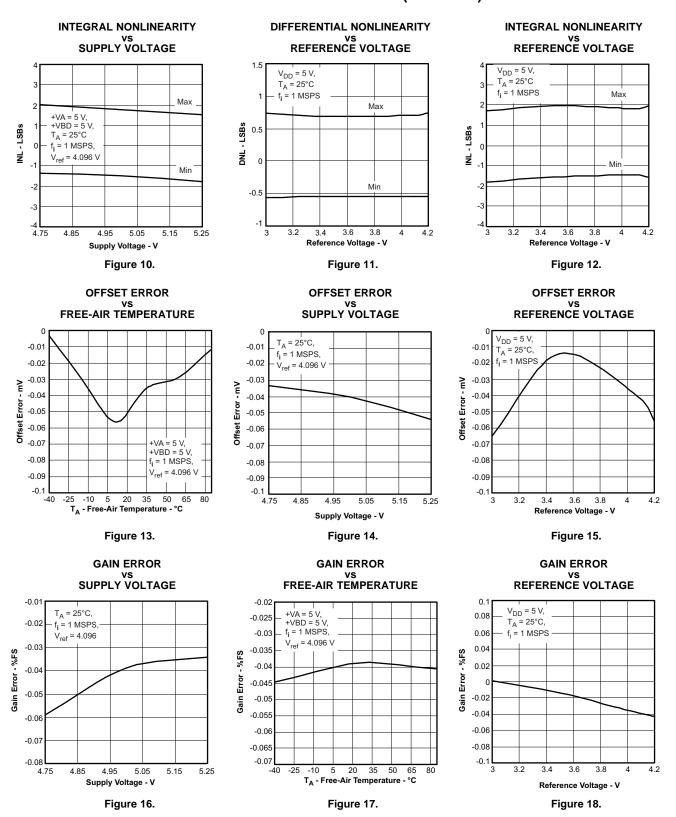


Figure 9.







## OFFSET ERROR TEMPERATURE DRIFT DISTRIBUTION (25 Samples)

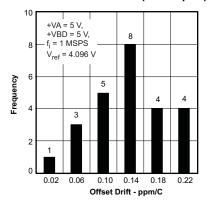


Figure 19.

## GAIN ERROR TEMPERATURE DRIFT DISTRIBUTION (25 Samples)

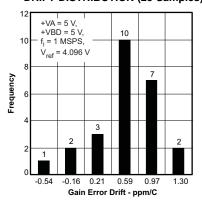


Figure 20.

TOTAL HARMONIC DISTORTION
VS
REFERENCE VOLTAGE

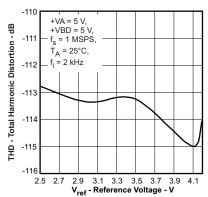


Figure 21.

## SIGNAL-TO-NOISE RATIO VS REFERENCE VOLTAGE

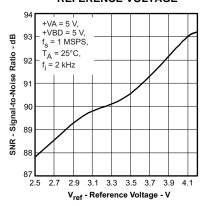


Figure 22.

#### SIGNAL-TO-NOISE + DISTORTION VS REFERENCE VOLTAGE

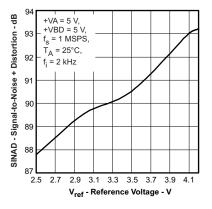


Figure 23.

# TOTAL HARMONIC DISTORTION vs FREE-AIR TEMPERATURE

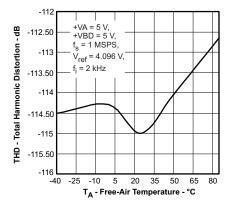


Figure 24.

## SPURIOUS FREE DYNAMIC RANGE vs FREE-AIR TEMPERATURE

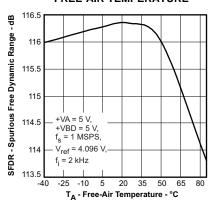


Figure 25.

#### SIGNAL-TO-NOISE RATIO VS FREE-AIR TEMPERATURE

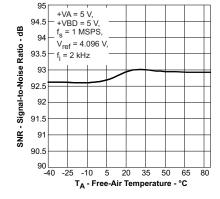


Figure 26.

#### SIGNAL-TO-NOISE + DISTORTION vs FREE-AIR TEMPERATURE

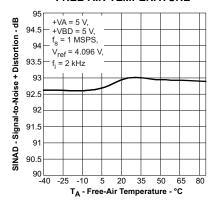
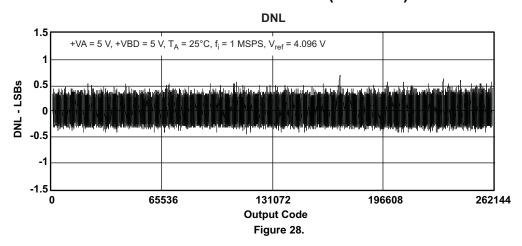
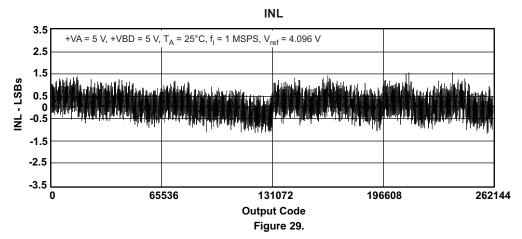
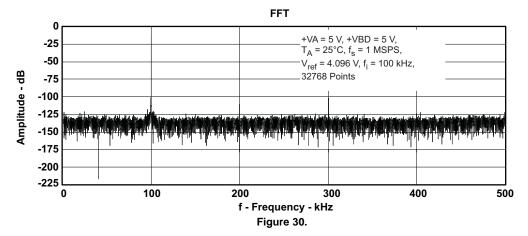


Figure 27.



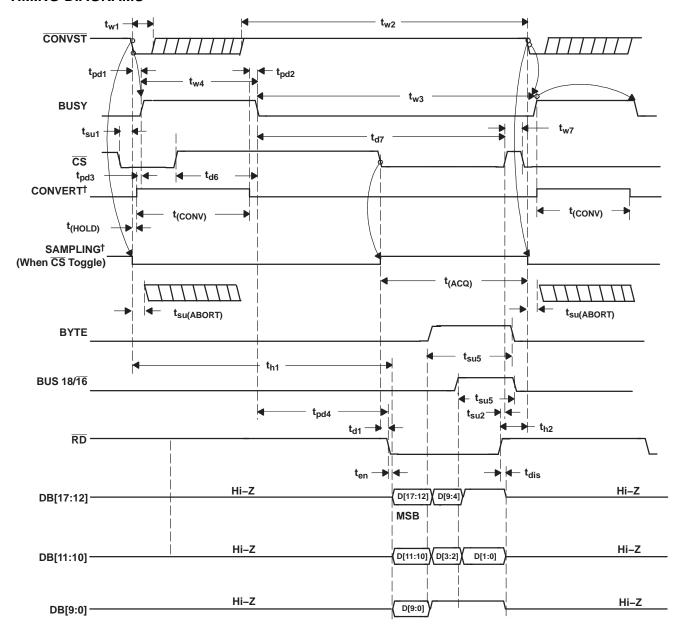








## **TIMING DIAGRAMS**



<sup>†</sup>Signal internal to device

Figure 31. Timing for Conversion and Acquisition Cycles With CS and RD Toggling



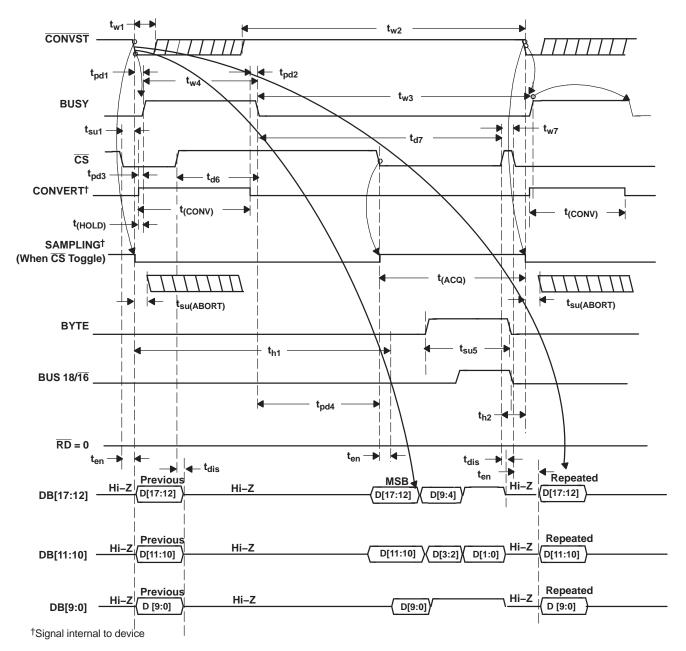
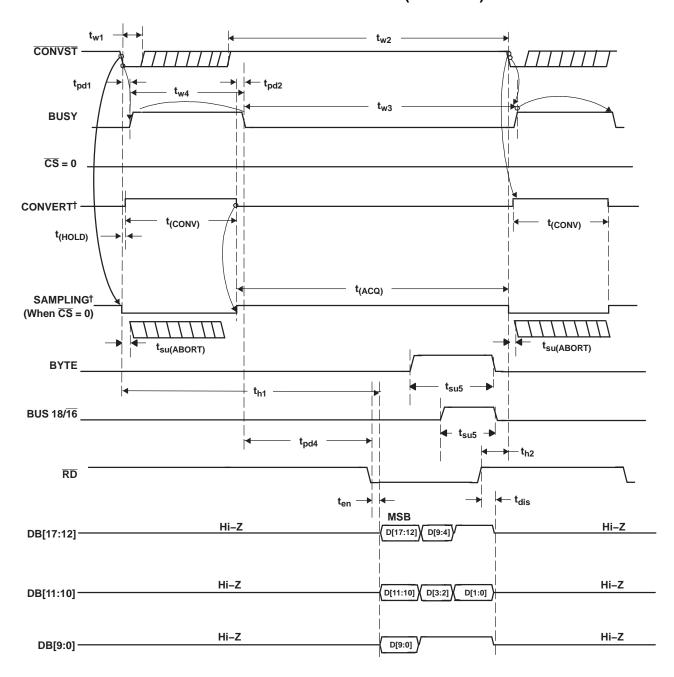


Figure 32. Timing for Conversion and Acquisition Cycles With CS Toggling, RD Tied to BDGND

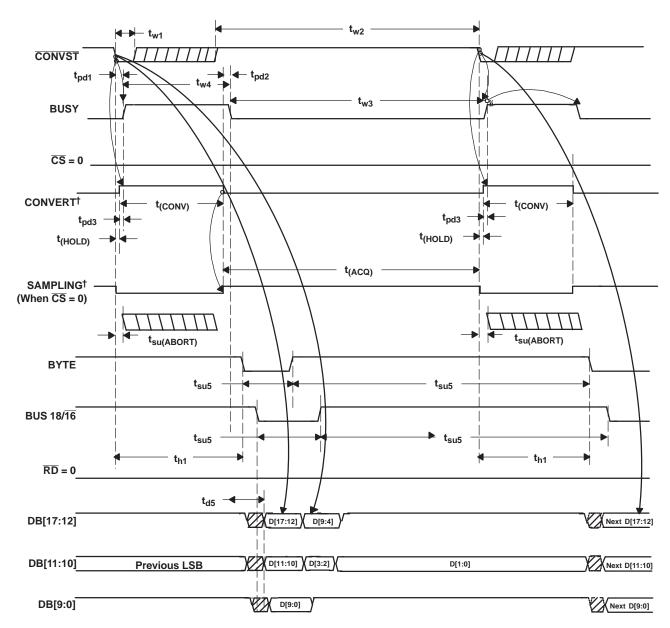




<sup>†</sup>Signal internal to device

Figure 33. Timing for Conversion and Acquisition Cycles With CS Tied to BDGND, RD Toggling





<sup>†</sup>Signal internal to device

Figure 34. Timing for Conversion and Acquisition Cycles With CS and RD Tied to BDGND - Auto Read



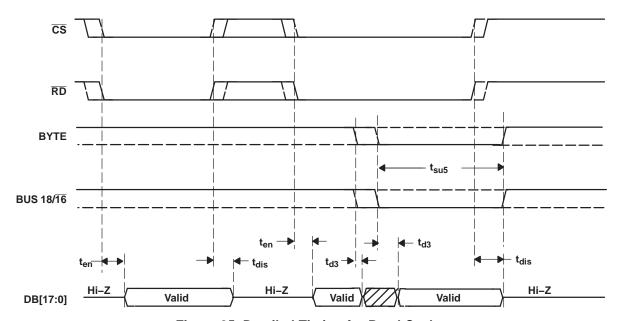


Figure 35. Detailed Timing for Read Cycles



## **APPLICATION INFORMATION**

## MICROCONTROLLER INTERFACING

## **ADS8481 to 8-Bit Microcontroller Interface**

Figure 36 shows a parallel interface between the ADS8481 and a typical microcontroller using the 8-bit data bus. The BUSY signal is used as a falling-edge interrupt to the microcontroller.

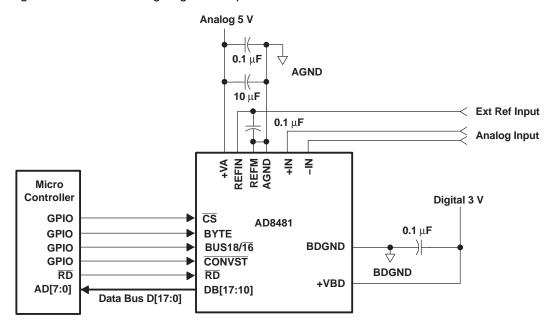


Figure 36. ADS8481 Application Circuitry

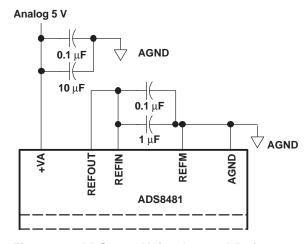


Figure 37. ADS8481 Using Internal Reference



### PRINCIPLES OF OPERATION

The ADS8481 is a high-speed successive approximation register (SAR) analog-to-digital converter (ADC). The architecture is based on charge redistribution which inherently includes a sample/hold function. See Figure 36 for the application circuit for the ADS8481.

The conversion clock is generated internally. The conversion time of 710 ns is capable of sustaining a 1 MHz throughput.

The analog input is provided to two input pins: +IN and -IN. When a conversion is initiated, the differential input on these pins is sampled on the internal capacitor array. While a conversion is in progress, both inputs are disconnected from any internal function.

### **REFERENCE**

The ADS8481 can operate with an external reference with a range from 3.0 V to 4.2 V. The reference voltage on the input pin #1 (REFIN) of the converter is internally buffered. A clean, low noise, well-decoupled reference voltage on this pin is required to ensure good performance of the converter. A low noise band-gap reference like the REF3240 can be used to drive this pin. A 0.1- $\mu$ F decoupling capacitor is required between REFIN and REFM pins (pin #13 and pin #12) of the converter. This capacitor should be placed as close as possible to the pins of the device. Designers should strive to minimize the routing length of the traces that connect the terminals of the capacitor to the pins of the converter. An RC network can also be used to filter the reference voltage. A 100- $\Omega$  series resistor and a 0.1- $\mu$ F capacitor, which can also serve as the decoupling capacitor can be used to filter the reference voltage.

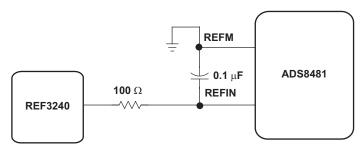


Figure 38. Reference Circuit

The ADS8481 also has limited low pass filtering capability built into the converter. The equivalent circuitry on the REFIN input is as shown in Figure 39.

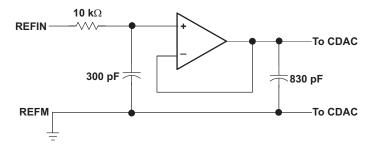


Figure 39. Reference Circuit

The REFM input of the ADS8481 should always be shorted to AGND.

A 4.096-V internal reference is included. When internal reference is used, pin 14 (REFOUT) is connected to pin 13 (REFIN) with a 0.1- $\mu$ F decoupling capacitor and 1-nF storage capacitor between pin 14 (REFOUT) and pins 11 and 12 (REFM) (see Figure Figure 37). The internal reference of the converter is double buffered. If an external reference is used, the second buffer provides isolation between the external reference and the CDAC. This buffer is also used to recharge all of the capacitors of the CDAC during conversion. Pin 14 (REFOUT) can be left unconnected (floating) if an external reference is used.



## PRINCIPLES OF OPERATION (continued)

#### ANALOG INPUT

When the converter enters the hold mode, the voltage difference between the +IN and -IN inputs is captured on the internal capacitor array. The voltage on the -IN input is limited between -0.2 V and 0.2 V, allowing the input to reject small signals which are common to both the +IN and -IN inputs. The +IN input has a range of -0.2 V to  $V_{ref}$  + 0.2 V. The input span [+IN - (-IN)] is limited to 0 V to  $V_{ref}$ .

The input current on the analog inputs depends upon a number of factors: sample rate, input voltage, and source impedance. Essentially, the current into the ADS8481 charges the internal capacitor array during the sample period. After this capacitance has been fully charged, there is no further input current. The source of the analog input voltage must be able to charge the input capacitance (65 pF) to an 18-bit settling level within the acquisition time (250 ns) of the device. When the converter goes into the hold mode, the input impedance is greater than 1  $G\Omega$ .

Care must be taken regarding the absolute analog input voltage. To maintain the linearity of the converter, the +IN and -IN inputs and the span [+IN - (-IN)] must be within the limits specified. Outside of these ranges, the converter's linearity may not meet specifications. To minimize noise, low bandwidth input signals with low-pass filters are used.

Care must be taken to ensure that the output impedance of the sources driving the +IN and -IN inputs are matched. If this is not observed, the two inputs could have different settling times. This may result in offset error, gain error, and linearity error which varies with temperature and input voltage.

The analog input to the converter needs to be driven with a low noise, high-speed op-amp like the THS4031. An RC filter is recommended at the input pins to low-pass filter the noise from the source. A series resistor of 20  $\Omega$  and a decoupling capacitor of 680 pF is recommended. The input to the converter is a uni-polar input voltage in the range 0 to  $V_{ref}$ . The THS4031 can be used in the source follower configuration to drive the converter.

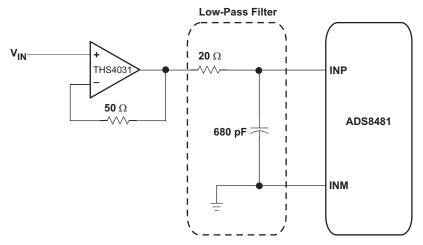


Figure 40. Input Circuit

In systems, where the input is bi-polar, the THS4031 can be used in the inverting configuration with an additional DC bias applied to its + input so as to keep the input to the ADS8481 within its rated operating voltage range. This configuration is also recommended when the ADS8481 is used in signal processing applications where good SNR and THD performance is required. The DC bias can be derived from the REF3220 or the REF3240 reference voltage ICs. The input configuration shown below is capable of delivering better than 92dB SNR and -100db THD at an input frequency of 100 kHz. In case band-pass filters are used to filter the input, care should be taken to ensure that the signal swing at the input of the band-pass filter is small so as to keep the distortion introduced by the filter minimal. In such cases, the gain of the circuit shown below can be increased to keep the input to the ADS8481 large to keep the SNR of the system high. Note that the gain of the system from the + input to the output of the THS4031 in such a configuration is a function of the gain of the AC signal. A resistor divider can be used to scale the output of the REF3220 or REF3240 to reduce the voltage at the DC input to THS4031 to keep the voltage at the input of the converter within its rated operating range.



## PRINCIPLES OF OPERATION (continued)

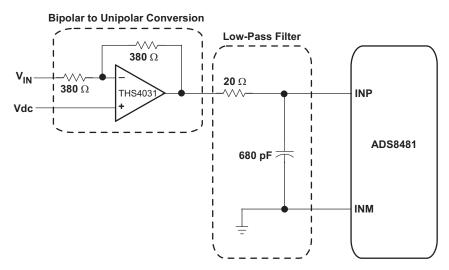


Figure 41. Input Circuit

### **DIGITAL INTERFACE**

### **Timing and Control**

See the timing diagrams in the specifications section for detailed information on timing signals and their requirements.

The ADS8481 uses an internal oscillator generated clock which controls the conversion rate and in turn the throughput of the converter. No external clock input is required.

Conversions are initiated by bringing the  $\overline{\text{CONVST}}$  pin low for a minimum of 20 ns (after the 20 ns minimum requirement has been met, the  $\overline{\text{CONVST}}$  pin can be brought high), while  $\overline{\text{CS}}$  is low. The ADS8481 switches from the sample to the hold mode on the falling edge of the  $\overline{\text{CONVST}}$  command. A clean and low jitter falling edge of this signal is important to the performance of the converter. The BUSY output is brought high immediately following  $\overline{\text{CONVST}}$  going low. BUSY stays high throughout the conversion process and returns low when the conversion has ended.

Sampling starts with the falling edge of the BUSY signal when  $\overline{\text{CS}}$  is tied low or starts with the falling edge of  $\overline{\text{CS}}$  when BUSY is low.

Both  $\overline{RD}$  and  $\overline{CS}$  can be high during and before a conversion with one exception ( $\overline{CS}$  must be low when  $\overline{CONVST}$  goes low to initiate a conversion). Both the  $\overline{RD}$  and  $\overline{CS}$  pins are brought low in order to enable the parallel output bus with the conversion.

## **Reading Data**

The ADS8481 outputs full parallel data in straight binary format as shown in Table 1. The parallel output is active when  $\overline{CS}$  and  $\overline{RD}$  are both low. There is a minimal quiet zone requirement around the falling edge of  $\overline{CONVST}$ . This is 50 ns prior to the falling edge of  $\overline{CONVST}$  and 40 ns after the falling edge. No data read should attempted within this zone. Any other combination of  $\overline{CS}$  and  $\overline{RD}$  sets the parallel output to 3-state. BYTE and BUS18/ $\overline{16}$  are used for multiword read operations. BYTE is used whenever lower bits on the bus are output on the higher byte of the bus. BUS18/ $\overline{16}$  is used whenever the last two bits on the 18-bit bus is output on either bytes of the higher 16-bit bus. Refer to Table 1 for ideal output codes.



		•	
DESCRIPTION	ANALOG VALUE	DIGITAL OUTPUT STRA	ICHT DINADY
Full scale range	+V <sub>ref</sub>	DIGITAL OUTPUT STRA	IGHT BINART
Least significant bit (LSB)	(+V <sub>ref</sub> )/262144	BINARY CODE	HEX CODE
+Full scale	(+V <sub>ref</sub> ) - 1 LSB	11 1111 1111 1111 1111	3FFFF
Midscale	(+V <sub>ref</sub> )/2	10 0000 0000 0000 0000	20000
Midscale – 1 LSB	(+V <sub>ref</sub> )/2 - 1 LSB	01 1111 1111 1111 1111	1FFFF
Zero	0.1/	00 0000 0000 0000 0000	00000

Table 1. Ideal Input Voltages and Output Codes

The output data is a full 18-bit word (D17-D0) on DB17-DB0 pins (MSB-LSB) if both BUS18/16 and BYTE are low

The result may also be read on an 16-bit bus by using only pins DB17–DB2. In this case two reads are necessary: the first as before, leaving both BUS18/ $\overline{16}$  and BYTE low and reading the 16 most significant bits (D17–D2) on pins DB17–DB2, then bringing BUS18/ $\overline{16}$  high while holding BYTE low. When BUS18/ $\overline{16}$  is high, the lower two bits (D1–D0) appear on pins DB3–DB2.

The result may also be read on an 8-bit bus for convenience. This is done by using only pins DB17–DB10. In this case three reads are necessary: the first as before, leaving both BUS18/16 and BYTE low and reading the 8 most significant bits on pins DB17–DB10, then bringing BYTE high while holding BUS18/16 low. When BYTE is high, the medium bits (D9–D2) appear on pins DB17–DB10. The last read is done by bringing BUS18/16 high while holding BYTE high. When BUS18/16 is high, the lower two bits (D1–D0) appear on pins DB11–DB10. The last read cycle is not necessary if only the first 16 most significant bits are of interest.

All of these multiword read operations can be performed with multiple active  $\overline{RD}$  (toggling) or with  $\overline{RD}$  held low for simplicity. This is referred to as the AUTO READ operation.

			DATA READ OUT						
ВҮТЕ	BUS18/16	PINS DB17-DB12	PINS DB11-DB10	PINS DB9-DB4	PINS DB3-DB2	PINS DB1-DB0			
High	High	All One's	D1-D0	All One's	All One's	All One's			
Low	High	All One's	All One's	All One's	D1-D0	All One's			
High	Low	D9-D4	D3-D2	All One's	All One's	All One's			
Low	Low	D17-D12	D11-D10	D9-D4	D3-D2	D1-D0			

**Table 2. Conversion Data Read Out** 

### **RESET**

On power-up, internal POWER-ON RESET circuitry generates the reset required for the device. The first three conversions after power-up are used to load factory trimming data for a specific device to assure high accuracy of the converter. The results of the first three conversions are invalid and should be discarded.

The device can also be reset through the use of the combination fo  $\overline{\text{CS}}$  and  $\overline{\text{CONVST}}$ . Since the BUSY signal is held at high during the conversion, either one of these conditions triggers an internal self-clear reset to the converter.

- Issue a CONVST when CS is low and the internal convert state is high. The falling edge of CONVST starts a reset.
- Issue a (select the device) while the internal convert state is high. The falling edge of (sauses a reset.

Once the device is reset, all output latches are cleared (set to zeroes) and the BUSY signal is brought low. A new sampling period is started at the falling edge of the BUSY signal immediately after the instant of the internal reset.



### **LAYOUT**

For optimum performance, care must be taken with the physical layout of the ADS8481 circuitry.

As the ADS8481 offers single-supply operation, it is often used in close proximity with digital logic, microcontrollers, microprocessors, and digital signal processors. The more digital logic present in the design and the higher the switching speed, the more difficult it is to achieve good performance from the converter.

The basic SAR architecture is sensitive to glitches or sudden changes on the power supply, reference, ground connections and digital inputs that occur just prior to latching the output of the analog comparator. Thus, driving any single conversion for an n-bit SAR converter, there are at least n windows in which large external transient voltages can affect the conversion result. Such glitches might originate from switching power supplies, nearby digital logic, or high power devices.

The degree of error in the digital output depends on the reference voltage, layout, and the exact timing of the external event.

On average, the ADS8481 draws very little current from an external reference as the reference voltage is internally buffered. If the reference voltage is external and originates from an op amp, make sure that it can drive the bypass capacitor or capacitors without oscillation. A  $0.1-\mu F$  capacitor is recommended from pin 13 (REFIN) directly to pin 12 (REFM). REFM and AGND must be shorted on the same ground plane under the device.

The AGND and BDGND pins should be connected to a clean ground point. In all cases, this should be the analog ground. Avoid connections which are too close to the grounding point of a microcontroller or digital signal processor. If required, run a ground trace directly from the converter to the power supply entry point. The ideal layout consists of an analog ground plane dedicated to the converter and associated analog circuitry.

As with the AGND connections, +VA should be connected to a 5-V power supply plane or trace that is separate from the connection for digital logic until they are connected at the power entry point. Power to the ADS8481 should be clean and well bypassed. A 0.1- $\mu$ F ceramic bypass capacitor should be placed as close to the device as possible. See Table 3 for the placement of the capacitor. In addition, a 1- $\mu$ F to 10- $\mu$ F capacitor is recommended. In some situations, additional bypassing may be required, such as a 100- $\mu$ F electrolytic capacitor or even a Pi filter made up of inductors and capacitors—all designed to essentially low-pass filter the 5-V supply, removing the high frequency noise.

**Table 3. Power Supply Decoupling Capacitor Placement** 

POWER SUPPLY PLANE	CONVERTER ANALOG SIDE	CONVERTER	
SUPPLY PINS	CONVERTER ANALOG SIDE	DIGITAL SIDE	
Pin pairs that require shortest path to decoupling capacitors	(7,8), (9,10), (16,17), (20,21), (22,23), (25,26)	36, 37	
Pins that require no decoupling	24, 26	1	







9-Jul-2017

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
ADS8481IBRGZT	ACTIVE	VQFN	RGZ	48	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ADS 8481I B	Samples
ADS8481IBRGZTG4	ACTIVE	VQFN	RGZ	48	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ADS 8481I B	Samples
ADS8481IRGZT	ACTIVE	VQFN	RGZ	48	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ADS 8481I	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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## **PACKAGE OPTION ADDENDUM**

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PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ADS8481IBRGZT	VQFN	RGZ	48	250	180.0	16.4	7.3	7.3	1.5	12.0	16.0	Q2
ADS8481IRGZT	VQFN	RGZ	48	250	180.0	16.4	7.3	7.3	1.5	12.0	16.0	Q2

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
ADS8481IBRGZT	VQFN	RGZ	48	250	213.0	191.0	55.0	
ADS8481IRGZT	VQFN	RGZ	48	250	213.0	191.0	55.0	



- NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Quad Flatpack, No-leads (QFN) package configuration.
  - D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
  - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
  - F. Falls within JEDEC MO-220.



## RGZ (S-PVQFN-N48)

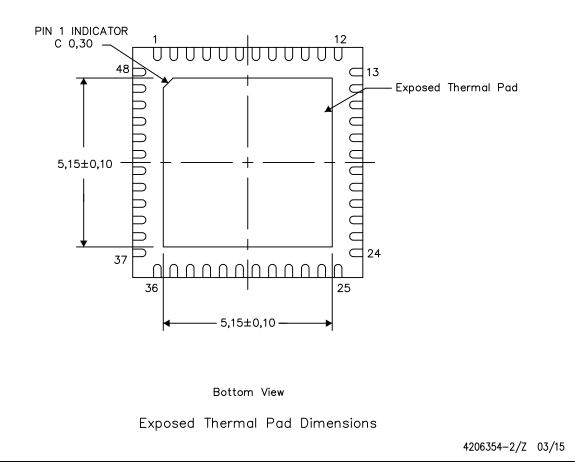
## PLASTIC QUAD FLATPACK NO-LEAD

### THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

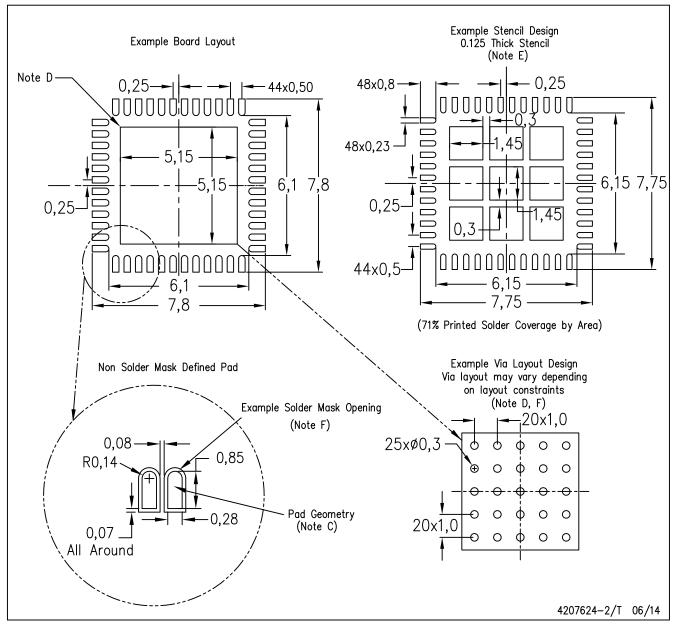


NOTE: All linear dimensions are in millimeters



## RGZ (S-PVQFN-N48)

## PLASTIC QUAD FLATPACK NO-LEAD



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat—Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in the thermal pad.



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